TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC5352

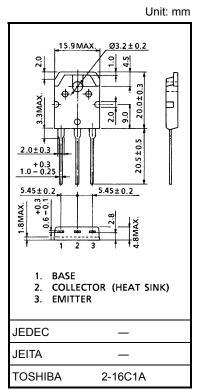
Switching Regulator and High-Voltage Switching Applications

High-Speed DC-DC Converter Applications

- Excellent switching times: t_r = 0.5 μs (max), t_f = 0.3 μs (max) (IC = 4 A)
- High breakdown voltage: VCEO = 400 V

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	600	٧	
Collector-emitter voltage		V _{CEO}	400	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC	I _C	10	Α	
	Pulse	I _{CP}	15		
Base current		Ι _Β	5	Α	
Collector power dissipation		P _C	80	W	
(Tc = 25°C)			80	۷V	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

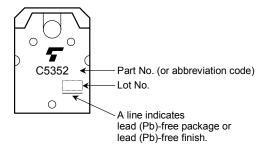


Weight: 4.7 g (typ.)

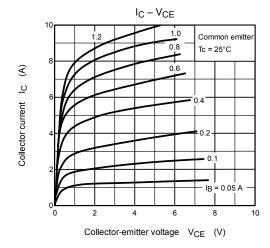
Electrical Characteristics (Tc = 25°C)

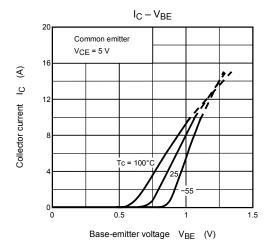
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I _{CBO}	V _{CB} = 480 V, I _E = 0	_	_	100	μΑ
Emitter cut-off cur	rent	I _{EBO}	V _{EB} = 7 V, I _C = 0	_	_	1	mA
Collector-base bro	eakdown voltage	V (BR) CBO	I _C = 1 mA, I _E = 0	600	_	_	V
Collector-emitter I	oreakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	400	_	_	٧
DC current gain		h _{FE}	V _{CE} = 5 V, I _C = 1 A	20	_	_	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 4 A, I _B = 0.5 A	_	_	1.0	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 4 A, I _B = 0.5 A	_	_	1.3	V
Switching time	Rise time	t _r	V _{CC} ≈ 200 V	_	_	0.5	
	Storage time	t _{stg}	20 μs I _C V Output	Ι	_	2.0	μs
	Fall time	t _f	I _{B2} I _{B1} = 0.5 A, I _{B2} = −1 A, duty cycle ≤ 1%	1	_	0.3	

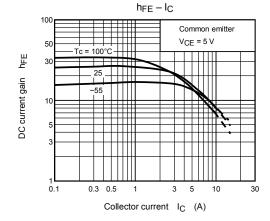
Marking

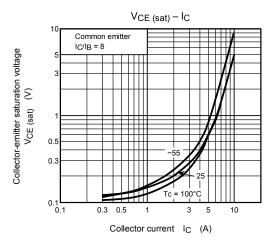


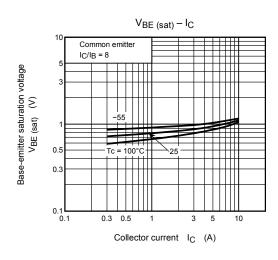
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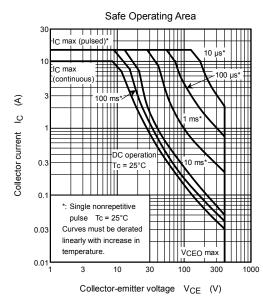












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